

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)		ATTY DOCKET NO. BHT/3230-63		APPLICATION NO. 10/625,516			
		APPLICANT TSUI					
		FILING DATE July 24, 2003			GROUP 2813		
Date Submitted to PTO: August 2, 2004		U.S. PATENT DOCUMENTS					
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
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OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
CAT		C.J. Koeneke, et al.; "Schottky MOSFET for VLSI"; in Dig. of IEDM, p. 367; 1981					
CAT		S.E. Swirhun et al.; "A VLSI Suitable Schottky Barrier CMOS Process"; IEEE, Trans. Electron Devices; Vol. ED-32, No. 2; p. 194; 1985					
CAT		B.Y. Tsui et al.; "A Novel Process For High-Performance Schottky Barrier PMOS"; J. Electrochem. Soc.; Vol. 136, No. 5; p. 1456; 1989					
CAT		C. Wang et al.; "Sub-50-nm PtSi Schottky Source/Drain p-MOSFETs"; in Proc. of Device Research Conf.; p/72; 1998					
CAT		C. Wang et al.; "Sub-50-nm PtSi Schottky Source/Drain Metal-Oxide-Semiconductor Field-Effect Transistors"; Appl. Phys. Lett.; Vol. 74, No. 8; p. 1174; 1999					
CAT		W. Saitoh et al. ; "35 nm Metal Gate SOI-p-MOSFETs With PtSi Schottky Source/Drain"; In Proc. of Device Research Conf.; p. 30; 1999					
CAT		A. Itoh et al.; "Very Short Channel Metal-Gate Schottky Source/Drain SOI-PMOSFETs And Their Short Channel Effect"; in Proc. of Device Research Conf.; p. 77; 2000					
CAT		H.C. Lin et al.; "A Novel Implantless MOS Thin-Film Transistor With Simple Processing, Excellent Performance, and Ambipolar Operation Capability"; in Dig. of IEDM; p. 857; 2000					
CAT		K. Uchida et al.; "Enhancement Of Hot-Electron Generation Rate in Schottky Source Metal-Oxide-Semiconductor Field-Effect Transistors"; Appl. Phys. Lett.; Vol. 76, No. 26; p. 3992; 2000					
EXAMINER	<i>Craig A. Thompson</i>			DATE CONSIDERED		8/20/04	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

AUG 8 2004

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